

SWITCHMODE SERIES

NPN SILICON POWER TRANSISTORS

The 2N6546 and 2N6547 transistors are designed for high-voltage, high-speed, power switching inductive circuits where fall time is critical. They are particularly suited for 115 and 220 volt line operated switch-mode applications such as:

- * Switching Regulators
- * PWM inverters and Motor Controls
- * Solenoid and Relay Drivers
- * Deflection Circuits

Boca Semiconductor Corp.
(BSC)

Specification Features-

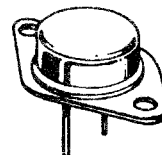
High Temperature Performance Specified for: Reversed Biased SOA with inductive loads
Switching Times with inductive Loads
Saturation Voltages, Leakage Currents.

NPN
2N6546
2N6547

15 AMPERE
NPN SILICON
POWER TRANSISTORS
300 - 400 VOLTS
175 WATTS

MAXIMUM RATINGS

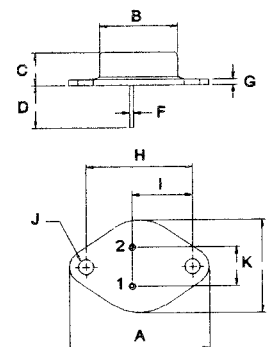
Characteristic	Symbol	2N6546	2N6547	Unit
Collector-Emitter Voltage	V_{CEO}	300	400	V
Collector-Emitter Voltage	V_{CEV}	650	850	V
Collector-Base Voltage	V_{EBO}	9.0		V
Collector current - Continuous	I_C	15		A
Collector current - Peak	I_{CM}	30		
Base current - Continuous	I_B	10		A
Emitter current - Continuous	I_E	25		A
Emitter current - Peak	I_{EM}	50		
Total Power Dissipation @ $T_c = 25^\circ\text{C}$ Derate above 25°C	P_D	175	1.0	W W/ $^\circ\text{C}$
Operating and Storage Junction Temperature Range	T_J, T_{STG}	- 65 to +200		$^\circ\text{C}$



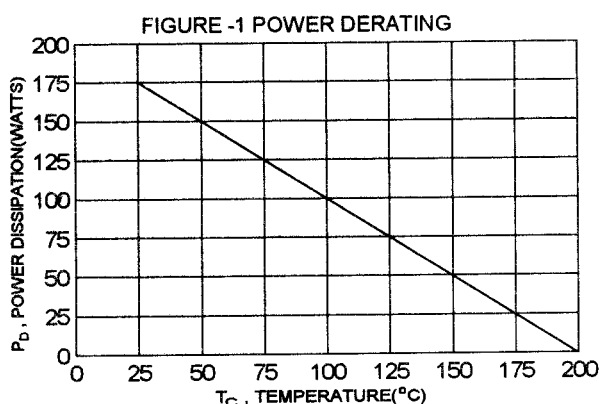
TO-3

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance Junction to Case	$R_{\theta jc}$	1.0	$^\circ\text{C}/\text{W}$



PIN 1.BASE
2.EMITTER
COLLECTOR(CASE)



DIM	MILLIMETERS	
	MIN	MAX
A	38.75	39.96
B	19.28	22.23
C	7.96	9.28
D	11.18	12.19
E	25.20	26.67
F	0.92	1.09
G	1.38	1.62
H	29.90	30.40
I	16.64	17.30
J	3.88	4.36
K	10.67	11.18

ELECTRICAL CHARACTERISTICS ($T_c = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
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OFF CHARACTERISTICS

Collector - Emitter Sustaining Voltage (1) ($I_c = 100\text{ mA}$, $I_B = 0$)	2N6546 2N6547	$V_{CEO(sus)}$	300 400	V
Collector Cutoff Current ($V_{CEV} = 650\text{ V}$, $V_{BE(off)} = 1.5\text{ V}$) ($V_{CEV} = 850\text{ V}$, $V_{BE(off)} = 1.5\text{ V}$) ($V_{CEV} = 650\text{ V}$, $V_{BE(off)} = 1.5\text{ V}$, $T_c = 100^\circ\text{C}$) ($V_{CEV} = 850\text{ V}$, $V_{BE(off)} = 1.5\text{ V}$, $T_c = 100^\circ\text{C}$)	2N6546 2N6547 2N6546 2N6547	I_{CEV}	1.0 1.0 4.0 4.0	mA
Emitter Cutoff Current ($V_{EB} = 9.0\text{ V}$, $I_c = 0$)		I_{EBO}	1.0	mA

ON CHARACTERISTICS(1)

DC Current Gain ($I_c = 5.0\text{ A}$, $V_{CE} = 2.0\text{ V}$) ($I_c = 10\text{ A}$, $V_{CE} = 2.0\text{ V}$)		hFE	12 6.0	60 30
Collector-Emitter Saturation Voltage ($I_c = 10\text{ A}$, $I_B = 2.0\text{ A}$) ($I_c = 15\text{ A}$, $I_B = 3.0\text{ A}$)		$V_{CE(sat)}$		1.5 5.0
Base-Emitter Saturation Voltage ($I_c = 10\text{ A}$, $I_B = 2.0\text{ A}$)		$V_{BE(sat)}$		1.6

DYNAMIC CHARACTERISTICS

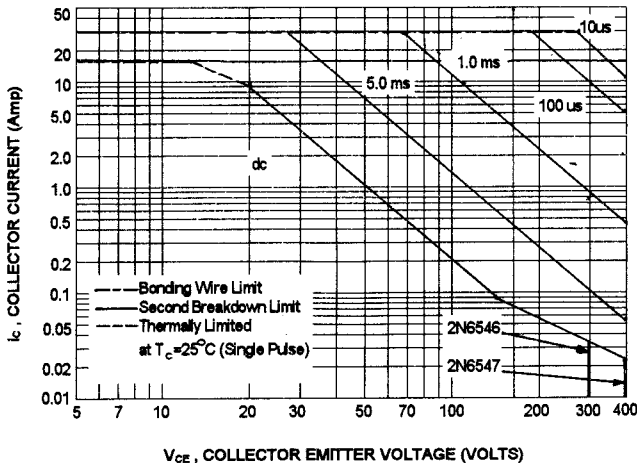
Current-Gain-Bandwidth Product (2) ($I_c = 500\text{ mA}$, $V_{CE} = 10\text{ V}$, $f = 1.0\text{ MHz}$)		f_T	6.0	35	MHz
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SWITCHING CHARACTERISTICS

Delay Time	$V_{CC} = 250\text{ V}$ $I_c = 10\text{ A}$ $I_{B1} = -I_{B2} = 2.0\text{ A}$ $t_p = 0.1\text{ ms}$ Duty Cycle $\leq 2.0\%$	t_d		0.05	us
Rise Time		t_r		1.0	us
Storage Time		t_s		4.0	us
Fall Time		t_f		0.8	us

(1) Pulse Test: Pulse width = 300 us , Duty Cycle $\leq 2.0\%$ (2) $f_T = |h_{fo}| \cdot f_{test}$

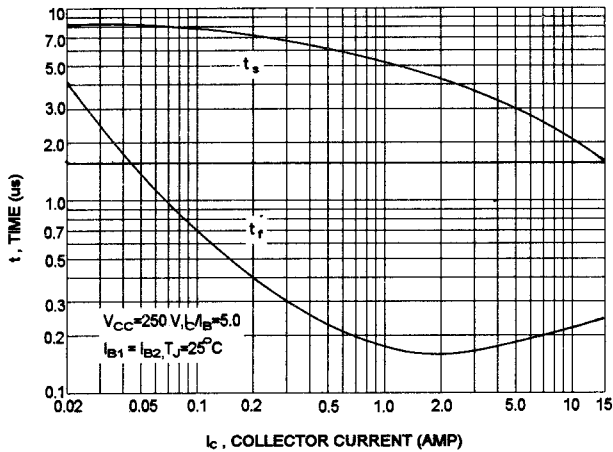
ACTIVE-REGION SAFE OPERATING AREA (SOA)



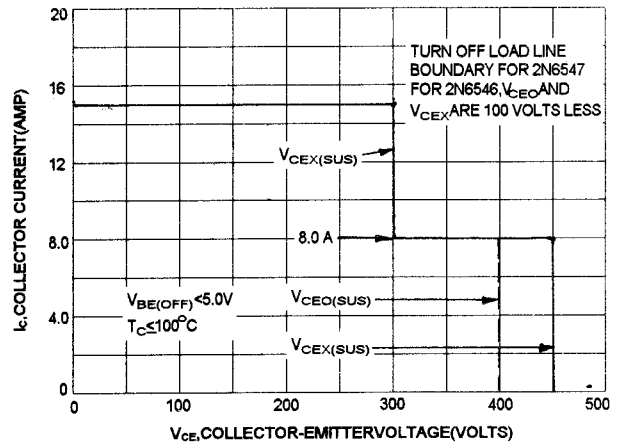
There are two limitation on the power handling ability of a transistor: average junction temperature and second breakdown safe operating area curves indicate I_C - V_{CE} limits of the transistor that must be observed for reliable operation i.e., the transistor must not be subjected to greater dissipation than curves indicate.

The data of SOA curve is base on $T_{J(PK)} = 200^\circ\text{C}$; T_C is variable depending on conditions. second breakdown pulse limits are valid for duty cycles to 10% provided $T_{J(PK)} \leq 200^\circ\text{C}$. At high case temperatures, thermal limitation will reduce the power that can be handled to values less than the limitations imposed by second breakdown.

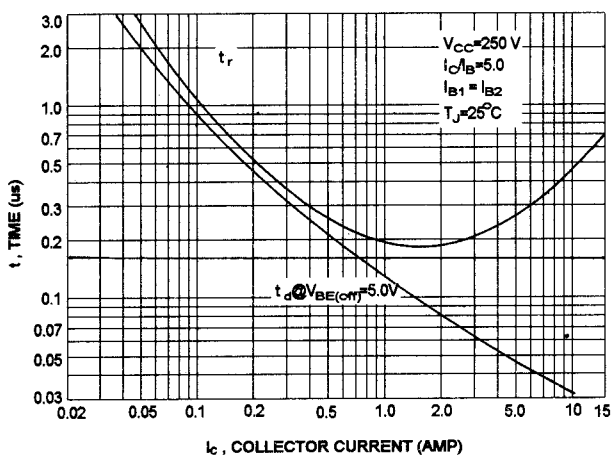
TURN-OFF TIME



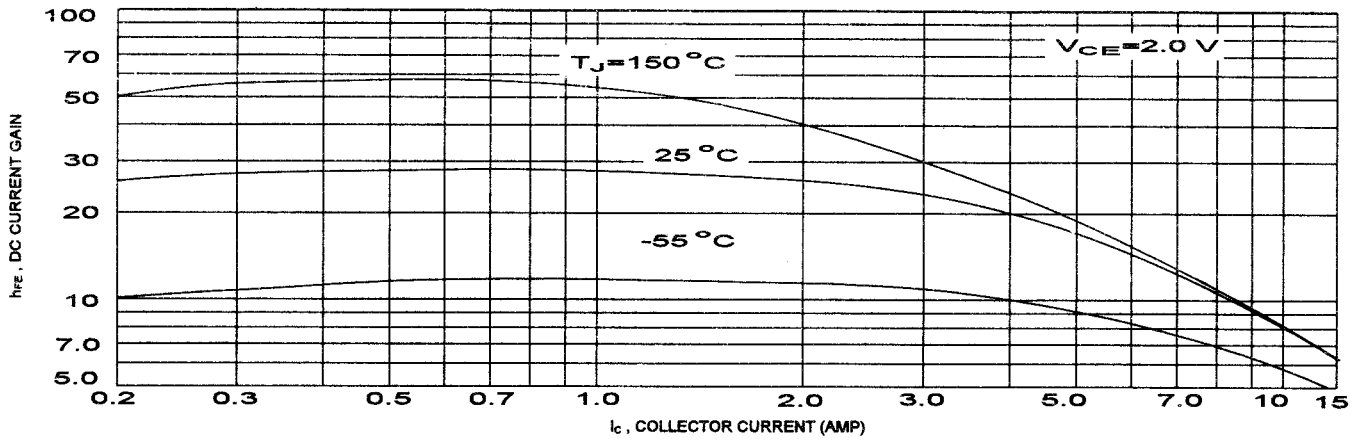
REVERSE BIAS SAFE OPERATING AREA



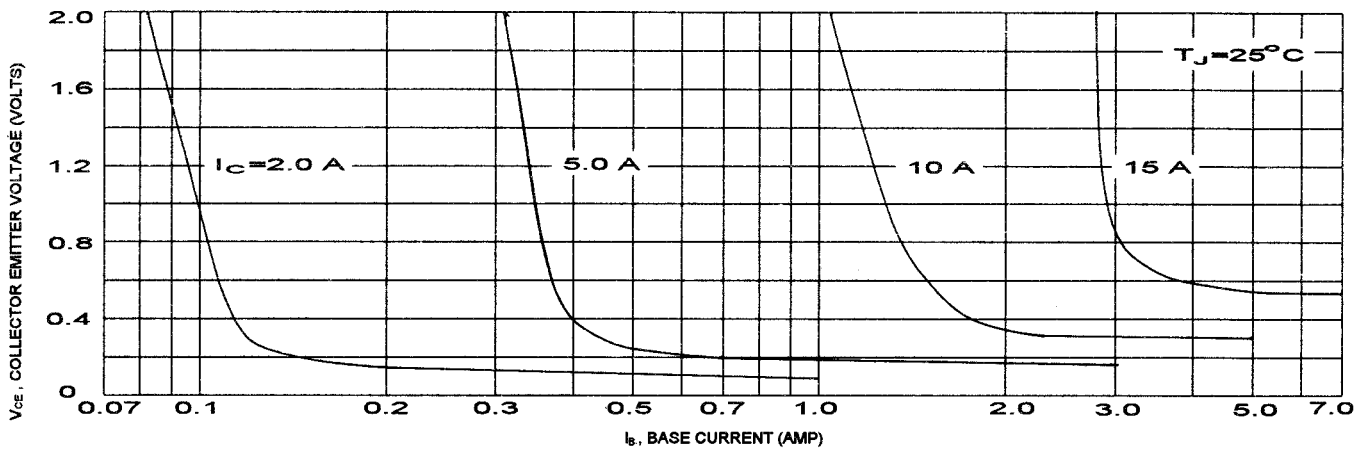
TURN-ON TIME



DC CURRENT GAIN



COLLECTOR SATURATION REGION



"ON" VOLTAGES

